# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



1N4531; 1N4532 High-speed diodes

Product specification Supersedes data of April 1996 1996 Sep 03





# **High-speed diodes**

1N4531; 1N4532

### **FEATURES**

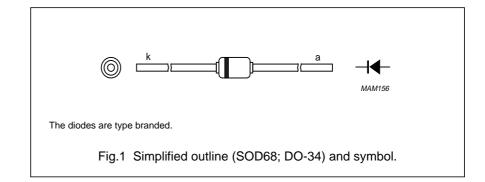
- Hermetically sealed leaded glass SOD68 (DO-34) package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA.

#### **APPLICATIONS**

- · High-speed switching
- Protection diodes in reed relays.

### **DESCRIPTION**

The 1N4531, 1N4532 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD68 (DO-34) packages.



### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage		_	75	V
V <sub>R</sub>	continuous reverse voltage		_	75	V
I <sub>F</sub>	continuous forward current	see Fig.2	_	200	mA
I <sub>FRM</sub>	repetitive peak forward current		_	450	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	A
		t = 1 ms	_	1	A
		t = 1 s	_	0.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		_	200	°C

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## **ELECTRICAL CHARACTERISTICS**

 $T_j$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 mA; see Fig.3	_	1000	mV
I <sub>R</sub>	reverse current	see Fig.5			
	IN4531	V <sub>R</sub> = 20 V	_	25	nA
		V <sub>R</sub> = 20 V; T <sub>j</sub> = 150 °C	_	50	μΑ
	IN4532	V <sub>R</sub> = 50 V	_	100	nA
		V <sub>R</sub> = 50 V; T <sub>j</sub> = 150 °C	_	100	μΑ
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.6			
	IN4531		_	4	pF
	IN4532		_	2	pF
t <sub>rr</sub>	reverse recovery time	when switched from I <sub>F</sub> = 10 mA to			
	IN4531	$I_R = 60 \text{ mA}; R_L = 100 \Omega;$	_	4	ns
	IN4532	measured at I <sub>R</sub> = 1 mA; see Fig.7	_	2	ns
	reverse recovery time	when switched from I <sub>F</sub> = 10 mA to			
	IN4532	$I_R = 10 \text{ mA}; R_L = 100 \Omega;$	_	4	ns
		measured at I <sub>R</sub> = 1 mA; see Fig.7			
$V_{fr}$	forward recovery voltage	when switched from $I_F = 100$ mA;	_	3	V
		$t_r \le 30$ ns; see Fig.8			

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length 5 mm	120	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	lead length 5 mm; note 1	350	K/W

# Note

1. Device mounted on a printed circuit-board without metallization pad.

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### **GRAPHICAL DATA**

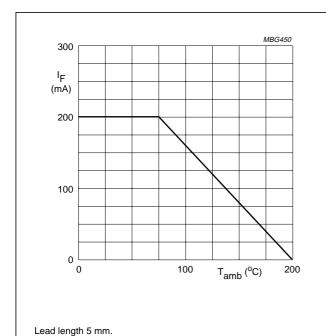
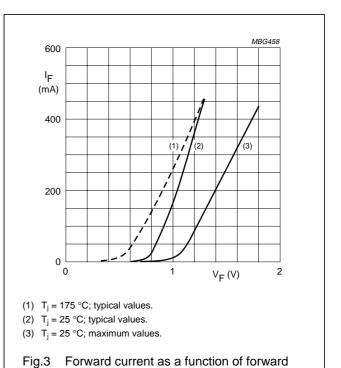
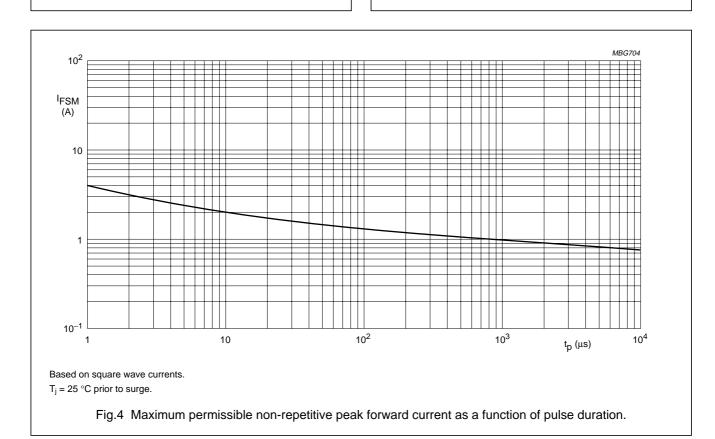


Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.

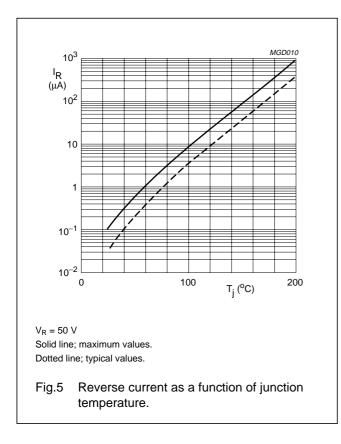


voltage.



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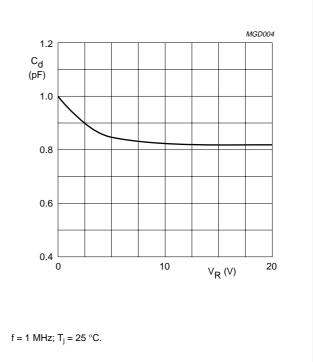
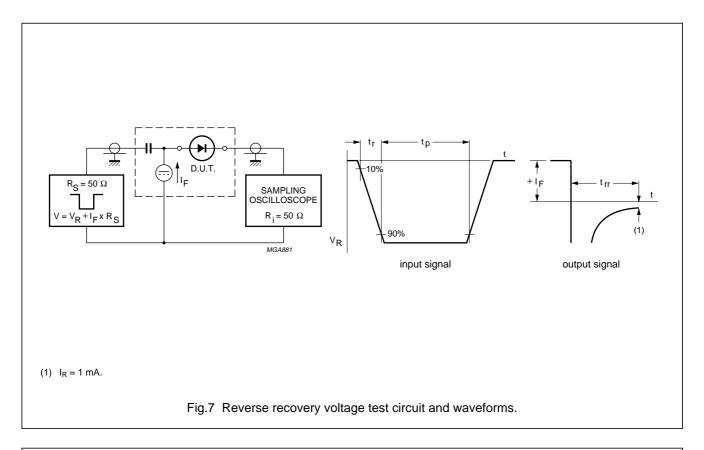
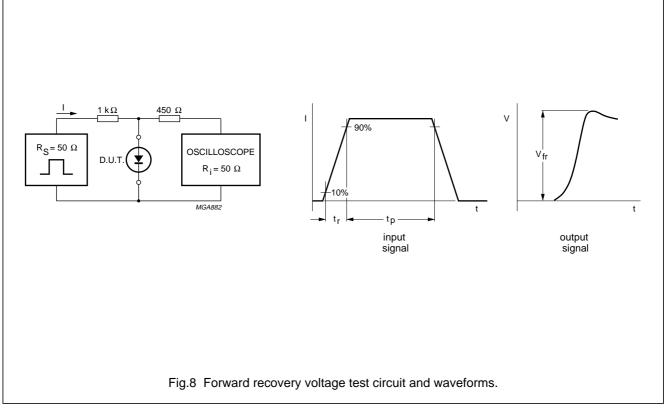


Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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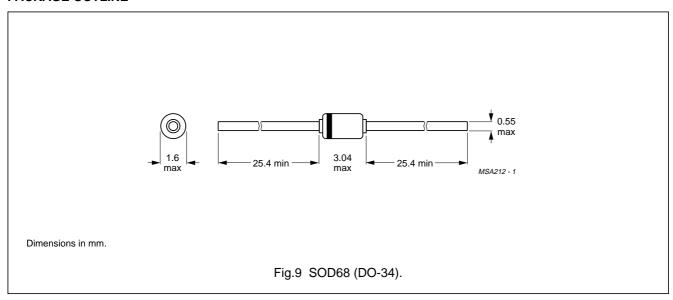
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#### **PACKAGE OUTLINE**



#### **DEFINITIONS**

Data Sheet Status			
Objective specification	This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.		
Product specification	This data sheet contains final product specifications.		
Limiting values			

#### **Limiting values**

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

## LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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